

Chun-Hu Cheng

List of Publications by Year in descending order

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158
papers

2,054
citations

279798

23
h-index

302126

39
g-index

159
all docs

159
docs citations

159
times ranked

2177
citing authors

#	ARTICLE	IF	CITATIONS
1	Low-Power High-Performance Non-Volatile Memory on a Flexible Substrate with Excellent Endurance. <i>Advanced Materials</i> , 2011, 23, 902-905.	21.0	130
2	Low-Voltage Steep Turn-On pMOSFET Using Ferroelectric High- κ Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2014, 35, 274-276.	3.9	112
3	Low-Leakage-Current DRAM-Like Memory Using a One-Transistor Ferroelectric MOSFET With a Hf-Based Gate Dielectric. <i>IEEE Electron Device Letters</i> , 2014, 35, 138-140.	3.9	110
4	A Flexible IGZO Thin-Film Transistor With Stacked TiO_2 -Based Dielectrics Fabricated at Room Temperature. <i>IEEE Electron Device Letters</i> , 2013, 34, 768-770.	3.9	103
5	Mechanism of GeO_2 resistive switching based on the multi-phonon assisted tunneling between traps. <i>Applied Physics Letters</i> , 2012, 100, 243506.	3.3	63
6	High Density and Low Leakage Current in TiO_2 MIM Capacitors Processed at 300 $^\circ\text{C}$. <i>IEEE Electron Device Letters</i> , 2008, 29, 845-847.	3.9	62
7	High Mobility Bilayer Metal-Oxide Thin Film Transistors Using Titanium-Doped InGaZnO. <i>IEEE Electron Device Letters</i> , 2014, 35, 87-89.	3.9	56
8	High-Temperature Leakage Improvement in Metal-Insulator-Metal Capacitors by Work-Function Tuning. <i>IEEE Electron Device Letters</i> , 2007, 28, 235-237.	3.9	51
9	Improved High-Temperature Leakage in High-Density MIM Capacitors by Using a TiLaO Dielectric and an Ir Electrode. <i>IEEE Electron Device Letters</i> , 2007, 28, 1095-1097.	3.9	46
10	$\text{Ni/GeO}_x/\text{TiO}_y/\text{TaN}$ RRAM on Flexible Substrate With Excellent Resistance Distribution. <i>IEEE Electron Device Letters</i> , 2013, 34, 505-507.	3.9	45
11	Progress and challenges in p-type oxide-based thin film transistors. <i>Nanotechnology Reviews</i> , 2019, 8, 422-443.	5.8	42
12	Influence of plasma fluorination on p-type channel tin-oxide thin film transistors. <i>Journal of Alloys and Compounds</i> , 2017, 707, 162-166.	5.5	39
13	Origin of traps and charge transport mechanism in hafnia. <i>Applied Physics Letters</i> , 2014, 105, 222901.	3.3	38
14	Ultralow Switching Energy $\text{Ni/GeO}_x/\text{HfON/TaN}$ RRAM. <i>IEEE Electron Device Letters</i> , 2011, 32, 366-368.	3.9	37
15	Use of a High-Work-Function Ni Electrode to Improve the Stress Reliability of Analog SrTiO_3 Metal-Insulator-Metal Capacitors. <i>IEEE Electron Device Letters</i> , 2007, 28, 694-696.	3.9	36
16	Long-Endurance Nanocrystal TiO_2 Resistive Memory Using a TaON Buffer Layer. <i>IEEE Electron Device Letters</i> , 2011, 32, 1749-1751.	3.9	34
17	Effect of Plasma Fluorination in p-Type SnO TFTs: Experiments, Modeling, and Simulation. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 1314-1321.	3.0	31
18	Charge transport in amorphous $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	29

#	ARTICLE	IF	CITATIONS
19	Fully room-temperature IGZO thin film transistors adopting stacked gate dielectrics on flexible polycarbonate substrate. <i>Solid-State Electronics</i> , 2013, 89, 194-197.	1.4	28
20	Investigation of strain-induced phase transformation in ferroelectric transistor using metal-nitride gate electrode. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1600368.	2.4	27
21	Thermal Leakage Improvement by Using a High-Work-Function Ni Electrode in High- κ TiHfO Metal-Insulator-Metal Capacitors. <i>Journal of the Electrochemical Society</i> , 2007, 154, G54.	2.9	26
22	Performance Enhancements in p-Type Al-Doped Tin-Oxide Thin Film Transistors by Using Fluorine Plasma Treatment. <i>IEEE Electron Device Letters</i> , 2017, 38, 210-212.	3.9	26
23	Energy-Efficient Versatile Memories With Ferroelectric Negative Capacitance by Gate-Strain Enhancement. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 3498-3501.	3.0	26
24	Implementation of Dopant-Free Hafnium Oxide Negative Capacitance Field-Effect Transistor. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 825-828.	3.0	25
25	Influence of CaCO ₃ and SiO ₂ additives on magnetic properties of M-type Sr ferrites. <i>Journal of Magnetism and Magnetic Materials</i> , 2018, 451, 288-294.	2.3	24
26	Evaluation of the nanoindentation behaviors of SiGe epitaxial layer on Si substrate. <i>Microelectronics Reliability</i> , 2010, 50, 63-69.	1.7	22
27	High-Performance Metal-Insulator-Metal Capacitors With $\text{HfTiO}_2/\text{Y}_2\text{O}_3$ Stacked Dielectric. <i>IEEE Electron Device Letters</i> , 2010, 31, 875-877.	3.9	21
28	Experimental Observation of Negative Capacitance Switching Behavior in One-Transistor Ferroelectric Versatile Memory. <i>Physica Status Solidi - Rapid Research Letters</i> , 2017, 11, 1700098.	2.4	21
29	Nanoscale potential fluctuation in non-stoichiometric HfO _x and low resistive transport in RRAM. <i>Microelectronic Engineering</i> , 2015, 147, 165-167.	2.4	20
30	Improvement of the Performance of TiHfO MIM Capacitors by Using a Dual Plasma Treatment of the Lower Electrode. <i>IEEE Electron Device Letters</i> , 2008, 29, 1105-1107.	3.9	19
31	Ultralow-Power Ni/GeO/STO/TaN Resistive Switching Memory. <i>IEEE Electron Device Letters</i> , 2010, 31, 1020-1022.	3.9	18
32	Fast Low-Temperature Plasma Process for the Application of Flexible Tin-Oxide-Channel Thin Film Transistors. <i>IEEE Nanotechnology Magazine</i> , 2017, 16, 876-879.	2.0	18
33	Flexible InGaZnO thin film transistors using stacked $\text{Y}_2\text{O}_3/\text{TiO}_2/\text{Y}_2\text{O}_3$ gate dielectrics grown at room temperature. <i>Physica Status Solidi - Rapid Research Letters</i> , 2013, 7, 285-288.	2.4	17
34	Energy-efficient HfAlO _x /NCFET: Using gate strain and defect passivation to realize nearly hysteresis-free sub-25mV/dec switch with ultralow leakage. , 2017, , .		17
35	Investigation of Gate-Stress Engineering in Negative Capacitance FETs Using Ferroelectric Hafnium Aluminum Oxides. <i>IEEE Transactions on Electron Devices</i> , 2019, 66, 1082-1086.	3.0	17
36	Magnetic property enhancement of cobalt-free M-type strontium hexagonal ferrites by CaCO ₃ and SiO ₂ addition. <i>Intermetallics</i> , 2017, 89, 111-117.	3.9	16

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37	Investigation of Double-Snapback Characteristic in Resistor-Triggered SCRs Stacking Structure. IEEE Transactions on Electron Devices, 2017, 64, 4200-4205.	3.0	16
38	Improved Stress Reliability of Analog TiHfO Metal-Insulator-Metal Capacitors Using High-Work-Function Electrode. Japanese Journal of Applied Physics, 2007, 46, 7300.	1.5	15
39	Highly scaled charge-trapping layer of ZrON nonvolatile memory device with good retention. Applied Physics Letters, 2010, 97, .	3.3	15
40	High performance IGZO/TiO ₂ thin film transistors using Y ₂ O ₃ buffer layers on polycarbonate substrate. Applied Physics A: Materials Science and Processing, 2013, 112, 817-820.	2.3	15
41	Structural stability of thermoelectric diffusion barriers: Experimental results and first principles calculations. Applied Physics Letters, 2013, 103, .	3.3	15
42	Percolation conductivity in hafnium sub-oxides. Applied Physics Letters, 2014, 105, 262903.	3.3	15
43	Highly uniform low-power resistive memory using nitrogen-doped tantalum pentoxide. Solid-State Electronics, 2012, 73, 60-63.	1.4	14
44	Low Operation Voltage InGaZnO Thin Film Transistors with LaAlO ₃ Gate Dielectric Incorporation. ECS Journal of Solid State Science and Technology, 2013, 2, N179-N181.	1.8	14
45	An Oxygen Gettering Scheme for Improving Device Mobility and Subthreshold Swing of InGaZnO-Based Thin-Film Transistor. IEEE Nanotechnology Magazine, 2014, 13, 933-938.	2.0	14
46	Low power 1T DRAM/NVM versatile memory featuring steep sub-60-mV/decade operation, fast 20-ns speed, and robust 85°C-extrapolated 10 ¹⁶ endurance. , 2015, , .		14
47	Bipolar Conduction in Tin-Oxide Semiconductor Channel Treated by Oxygen Plasma for Low-Power Thin-Film Transistor Application. Journal of Display Technology, 2016, 12, 224-227.	1.2	14
48	Improvement of dielectric flexibility and electrical properties of mechanically flexible thin film devices using titanium oxide materials fabricated at a very low temperature of 100°C. Journal of Alloys and Compounds, 2015, 643, S133-S136.	5.5	13
49	Investigation on polarization characteristics of ferroelectric memories with thermally stable hafnium aluminum oxides. Vacuum, 2019, 166, 11-14.	3.5	13
50	Low-Threshold-Voltage TaN/LaTiO n-MOSFETs With Small EOT. IEEE Electron Device Letters, 2009, 30, 999-1001.	3.9	12
51	Amorphous bilayer TiO ₂ -InGaZnO thin film transistors with low drive voltage. Solid-State Electronics, 2014, 99, 51-54.	1.4	12
52	Improved current distribution in resistive memory on flexible substrate using nitrogen-rich TaN electrode. Applied Physics Letters, 2012, 101, .	3.3	11
53	Room-temperature flexible thin film transistor with high mobility. Current Applied Physics, 2013, 13, 1459-1462.	2.4	11
54	Leakage Current Improvement of Ni-TiNiO-TaN Metal-Insulator-Metal Capacitors using Optimized N ⁺ Plasma Treatment and Oxygen Annealing. Electrochemical and Solid-State Letters, 2007, 10, H287.	2.2	10

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55	High Mobility Field-Effect Thin Film Transistor Using Room-Temperature High- κ Gate Dielectrics. Journal of Display Technology, 2014, 10, 875-881.	1.2	10
56	Nanotribological properties of ALD-processed bilayer TiO ₂ /ZnO films. Microelectronics Reliability, 2014, 54, 2754-2759.	1.7	10
57	Low power resistive random access memory using interface-engineered dielectric stack of SiO _x /a-Si/TiO _y with 1D1R-like structure. Current Applied Physics, 2014, 14, 139-143.	2.4	10
58	Physical Modeling of p-Type Fluorinated Al-Doped Tin-Oxide Thin Film Transistors. IEEE Journal of the Electron Devices Society, 2020, 8, 948-958.	2.1	10
59	Structural stability of diffusion barriers in thermoelectric SbTe: From first-principles calculations to experimental results. Journal of Alloys and Compounds, 2014, 588, 633-637.	5.5	9
60	High-Performance MIM Capacitors Using a High- κ TiZrO Dielectric. Journal of the Electrochemical Society, 2008, 155, G295.	2.9	8
61	High-Performance Metal-Insulator-Metal Capacitor Using Quality Properties of High- κ TiPrO Dielectric. Journal of the Electrochemical Society, 2009, 156, G23.	2.9	8
62	Nano-crystallized titanium oxide resistive memory with uniform switching and long endurance. Applied Physics A: Materials Science and Processing, 2013, 111, 203-207.	2.3	8
63	Gate-first n-MOSFET with a sub-0.6-nm EOT gate stack. Microelectronic Engineering, 2013, 109, 35-38.	2.4	8
64	Improved high-temperature switching characteristics of Y ₂ O ₃ /TiO _x resistive memory through carrier depletion effect. Physica Status Solidi - Rapid Research Letters, 2014, 8, 431-435.	2.4	8
65	Investigation of mechanical bending instability in flexible low-temperature-processed electrochromic display devices. Thin Solid Films, 2015, 584, 94-97.	1.8	8
66	A highly scalable poly-Si junctionless FETs featuring a novel multi-stacking hybrid P/N layer and vertical gate with very high I _{on} /I _{off} for 3D stacked ICs. , 2016, , .		8
67	p-type tin oxide thin film transistors for blue-light detection application. Physica Status Solidi - Rapid Research Letters, 2016, 10, 919-923.	2.4	8
68	Effect of specific surface area of raw material Fe ₂ O ₃ on magnetic properties of YIG. Journal of Magnetism and Magnetic Materials, 2018, 449, 157-164.	2.3	8
69	Impact of Zirconium Doping on Steep Subthreshold Switching of Negative Capacitance Hafnium Oxide Based Transistors. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800573.	2.4	8
70	A Study on Frequency-Dependent Voltage Nonlinearity of SrTiO ₃ rf Capacitor. Electrochemical and Solid-State Letters, 2010, 13, H436.	2.2	7
71	Low-Voltage InGaZnO Thin Film Transistors with Small Sub-Threshold Swing. Journal of Nanoscience and Nanotechnology, 2015, 15, 1486-1489.	0.9	7
72	Gettering Effect Induced by Oxygen-Deficient Titanium Oxide in InZnO and InGaZnO Channel Systems for Low-Power Display Applications. Journal of Display Technology, 2016, 12, 219-223.	1.2	7

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73	Achieving High-Scalability Negative Capacitance FETs with Uniform Sub-35 mV/dec Switch Using Dopant-Free Hafnium Oxide and Gate Strain. , 2018, , .		7
74	Negative Capacitance CMOS Field-Effect Transistors with Non-Hysteretic Steep Sub-60mV/dec Swing and Defect-Passivated Multidomain Switching. , 2019, , .		7
75	High-field mobility metal-gate/high- \hat{p} Ge n-MOSFETs with small equivalent-oxide-thickness. Solid-State Electronics, 2011, 55, 64-67.	1.4	6
76	Interface engineering of ferroelectric negative capacitance FET for hysteresis-free switch and reliability improvement. , 2018, , .		6
77	Effect of plasma oxidation on tin-oxide active layer for thin-film transistor applications. Journal of Materials Science, 2021, 56, 6286-6291.	3.7	6
78	Bipolar switching characteristics of low-power GeO resistive memory. Solid-State Electronics, 2011, 62, 90-93.	1.4	5
79	Nanotribological behavior of ZnO films prepared by atomic layer deposition. Journal of Physics and Chemistry of Solids, 2014, 75, 334-338.	4.0	5
80	Performance improvement of electrochromic display devices employing micro-size precipitates of tungsten oxide. Applied Physics A: Materials Science and Processing, 2014, 116, 1553-1559.	2.3	5
81	Correlation of thermal annealing effect, crystallinity and electrical characteristics in c-axis crystallized InGaZnO thin-film transistors. Journal of Alloys and Compounds, 2015, 643, S187-S192.	5.5	5
82	One-transistor ferroelectric versatile memory: Strained-gate engineering for realizing energy-efficient switching and fast negative-capacitance operation. , 2016, , .		5
83	Development of Optimum Preparation Conditions of Fe-Deficient M-Type Ca \hat{e} “Sr \hat{e} “La System Hexagonal Ferrite Magnet. IEEE Transactions on Magnetics, 2021, 57, 1-7.	2.1	5
84	Simultaneous Analysis of Multi-Variables Effect on the Performance of Multi-Domain MFIS Negative Capacitance Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2021, 9, 741-747.	2.1	5
85	Low-Threshold-Voltage TaN/Ir/LaTiO p-MOSFETs Incorporating Low-Temperature-Formed Shallow Junctions. IEEE Electron Device Letters, 2009, 30, 681-683.	3.9	4
86	High-Performance Gate-First Epitaxial Ge n-MOSFETs on Si With LaAlO_3 Gate Dielectrics. IEEE Transactions on Electron Devices, 2010, 57, 3525-3530.	3.0	4
87	High Capacitance Density and Thermal Leakage Improvement by Using High- \hat{p} Al ₂ O ₃ -Doped SrTiO ₃ MIM Capacitors. Journal of the Electrochemical Society, 2010, 157, H624.	2.9	4
88	Sub-micro watt resistive memories using nano-crystallized aluminum oxynitride dielectric. Applied Physics A: Materials Science and Processing, 2014, 116, 575-579.	2.3	4
89	Operation mechanism investigation of electrochromic display devices using tungsten oxides based on solid-state metal-oxide-metal capacitor structures. Solid-State Electronics, 2014, 99, 16-20.	1.4	4
90	Channel Modification Engineering by Plasma Processing in Tin-Oxide Thin Film Transistor: Experimental Results and First-Principles Calculation. ECS Journal of Solid State Science and Technology, 2017, 6, Q53-Q57.	1.8	4

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91	Effect of body bias and temperature on low-frequency noise in 40-nm nMOSFETs. <i>Microelectronics Reliability</i> , 2017, 78, 267-271.	1.7	4
92	Direct Fabrication of Inkjet-Printed Dielectric Film for Metal-Insulator-Metal Capacitors. <i>Journal of Electronic Materials</i> , 2018, 47, 677-683.	2.2	4
93	Investigation of Phase Transformation in HfO ₂ Ferroelectric Capacitor by Means of a ZrO ₂ Capping Layer. , 2019, , .		4
94	Forming-Free SiGeO _x /TiO _y Resistive Random Access Memories Featuring Large Current Distribution Windows. <i>Journal of Nanoscience and Nanotechnology</i> , 2019, 19, 7916-7919.	0.9	4
95	Improved Negative-Capacitance Switch of Ferroelectric Field Effect Transistor Using Defect Passivation Engineering. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1800493.	2.4	4
96	Characteristic Simulation of Hybrid Multilayer Junctionless Field Effect Transistors with Negative Capacitance Effect. <i>IEEE Nanotechnology Magazine</i> , 2020, 19, 89-93.	2.0	4
97	Impact of stress and doping effects on the polarization behavior and electrical characteristics of hafnium-zirconium oxides. <i>Ceramics International</i> , 2021, 47, 2864-2868.	4.8	4
98	Performance Improvement of Metal-Insulator-Metal Capacitors Using Postmetallization-Annealed Treatment on the Al ₂ O ₃ •TiO ₂ •Al ₂ O ₃ Film. <i>Electrochemical and Solid-State Letters</i> , 2009, 12, H123.	2.2	3
99	High performance metal/insulator/metal capacitors using HfTiO as dielectric. , 2009, , .		3
100	Lanthanide-Oxides Mixed TiO ₂ Dielectrics for High- ϵ_r MIM Capacitors. <i>Journal of the Electrochemical Society</i> , 2010, 157, H821.	2.9	3
101	Schottky-Barrier Resistive Memory with Highly Uniform Switching. <i>Journal of Nanoscience and Nanotechnology</i> , 2014, 14, 5166-5170.	0.9	3
102	Impact of nanoscale polarization relaxation on endurance reliability of one-transistor hybrid memory using combined storage mechanisms. , 2015, , .		3
103	Temperature-Dependent Transfer Characteristics of Low Turn-On Voltage InGaZnO Metal-Oxide Devices With Thin Titanium Oxide Capping Layers. <i>Journal of Display Technology</i> , 2015, 11, 512-517.	1.2	3
104	Ultrasonic dissimilar joining of aluminum alloy and polymer with the composite material of ABS polymer doping carbonized rice husk. <i>MATEC Web of Conferences</i> , 2017, 130, 06001.	0.2	3
105	Investigation of Polarization Hysteresis and Transient Current Switching in Ferroelectric Aluminum-Doped Hafnium Oxides. , 2018, , .		3
106	Improved Thermal Stability and Stress Immunity in Highly Scalable Junctionless FETs Using Enhanced-Depletion Channels. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, Q242-Q245.	1.8	3
107	On the Electrical Characteristics of Ferroelectric FinFET Using Hafnium Zirconium Oxide with Optimized Gate Stack. <i>ECS Journal of Solid State Science and Technology</i> , 2018, 7, P640-P646.	1.8	3
108	Stabilizing Ferroelectric Domain Switching of Hafnium Aluminum Oxide Using Metal Nitride Electrode Engineering. <i>ECS Journal of Solid State Science and Technology</i> , 2019, 8, P553-P556.	1.8	3

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109	High performance negative capacitance field-effect transistor featuring low off-state current, high on/off current ratio, and steep sub-60 mV dec ⁻¹ swing. Japanese Journal of Applied Physics, 2020, 59, SGGA01.	1.5	3
110	Preparation and magnetic properties of high performance Ca-Sr based M-type hexagonal ferrites. Results in Materials, 2020, 8, 100150.	1.8	3
111	Impact of Series-Connected Ferroelectric Capacitor in HfO ₂ -Based Ferroelectric Field-Effect Transistors for Memory Application. IEEE Journal of the Electron Devices Society, 2020, 8, 1076-1081.	2.1	3
112	A p-type Ferroelectric Field-Effect Transistor Using Ultrathin Hafnium Aluminum Oxide. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000356.	2.4	3
113	A comparative study of metal-ferroelectric-metal devices using doped- and stacked-hafnium zirconium oxides. Thin Solid Films, 2020, 701, 137927.	1.8	3
114	Effect of capping layer on the ferroelectricity of hafnium oxide. Thin Solid Films, 2022, 753, 139274.	1.8	3
115	Effect of Ta ₂ O ₅ Doping on Electrical Characteristics of SrTiO ₃ Metal-Insulator-Metal Capacitors. Japanese Journal of Applied Physics, 2009, 48, 081401.	1.5	2
116	Higher- κ titanium dioxide incorporating LaAlO ₃ as dielectrics for MIM capacitors. Solid-State Electronics, 2010, 54, 646-649.	1.4	2
117	Unipolar Ni/CeO _x /PbZr _{0.5} Ti _{0.5} O ₃ /TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2
118	Characteristics of 4H-SiC RF MOSFETs on a Semi-Insulating Substrate. ECS Transactions, 2011, 35, 173-183.	0.5	2
119	Achieving low sub-0.6-nm EOT in gate-first n-MOSFET with TiLaO/CeO ₂ gate stack. Solid-State Electronics, 2013, 82, 111-114.	1.4	2
120	Interface-engineered resistive memory using plasma-modified electrode on polyimide substrate. Physica Status Solidi - Rapid Research Letters, 2014, 8, 100-104.	2.4	2
121	The Role of Oxygen Vacancies on Switching Characteristics of TiO ₂ /Al ₂ O ₃ /TiO ₂ Resistive Memories. Journal of Nanoscience and Nanotechnology, 2015, 15, 4431-4434.	0.9	2
122	TiO ₂ -Based Indium Phosphide Metal-Oxide-Semiconductor Capacitor with High Capacitance Density. Journal of Nanoscience and Nanotechnology, 2015, 15, 2810-2813.	0.9	2
123	Structural and electrical characteristics of thin film transistor employing an oriented crystalline InGaZnO channel. Japanese Journal of Applied Physics, 2015, 54, 04DF05.	1.5	2
124	Investigation of Electrical Characteristics on 25-nm InGaAs Channel FinFET Using InAlAs Back Barrier and Al ₂ O ₃ Gate Dielectric. ECS Journal of Solid State Science and Technology, 2017, 6, Q58-Q62.	1.8	2
125	Using nanoindentation to investigate the temperature cycling of Sn 37Pb solders. Microelectronics Reliability, 2017, 78, 111-117.	1.7	2
126	Impact of ferroelectric domain switching in nonvolatile charge-trapping memory. , 2017, , .		2

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127	Paraelectric-Ferroelectric Transition in Hafnium-Oxide-Based Ferroelectric Memory. , 2018, , .		2
128	Unipolar Ni/GeO _x /PbZr _{0.5} Ti _{0.5} O ₃ /TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2
129	High- $\hat{\rho}$ TiCeO MIM Capacitors with a Dual-Plasma Interface Treatment. Electrochemical and Solid-State Letters, 2010, 13, H112.	2.2	1
130	Evaluation of Temperature Stability of Trilayer Resistive Memories Using Work-Function Tuning. Applied Physics Express, 2013, 6, 041203.	2.4	1
131	Crystallized Ohmic Contact Effect in AlGaIn/GaN High Electron Mobility Transistor. Japanese Journal of Applied Physics, 2013, 52, 081001.	1.5	1
132	Performance comparison of titanium-oxide resistive switching memories using GeO _x and AlO _x capping layers for flexible application. Japanese Journal of Applied Physics, 2014, 53, 061502.	1.5	1
133	Amorphous Titanium Oxide Semiconductors on Quasi-Crystal-Like InGaZnO Channels for Thin Film Transistor Applications. Journal of Display Technology, 2015, 11, 506-511.	1.2	1
134	Interface polarization fluctuation effect of ferroelectric hafnium-zirconium-oxide ferroelectric memory with nearly ideal subthreshold slope. , 2015, , .		1
135	High holding voltage segmentation stacking silicon-controlled-rectifier structure with field implant as body ties blocking layer. Japanese Journal of Applied Physics, 2016, 55, 04ER10.	1.5	1
136	A high output power and low phase noise GaN HEMT VCO with array of switchable inductors. International Journal of Circuit Theory and Applications, 2017, 45, 1621-1636.	2.0	1
137	Program/erase speed and data retention trade-off in negative capacitance versatile memory. , 2017, , .		1
138	Electrical Characteristics Investigation of Ferroelectric Memories Using Stacked and Mixed Hafnium Zirconium Oxides. Thin Solid Films, 2022, , 139395.	1.8	1
139	Low-Voltage Organic Thin-Film Transistor With High- $\hat{\rho}$ LaYOx Gate Insulator. ECS Transactions, 2008, 16, 231-237.	0.5	0
140	Improved Lower Electrode Oxidation of High-k TiCeO Metal-Insulator-Metal Capacitors by Using Dual Plasma Treatment. ECS Transactions, 2009, 16, 323-333.	0.5	0
141	Flow Rate's Influence on Low Temperature Silicon Oxide Deposited by Atmospheric Pressure Plasma Jet for Organic Thin Film Transistor Application. ECS Transactions, 2010, 33, 255-264.	0.5	0
142	The Reliability Study and Device Modeling for p-HEMT Microwave Power Transistors. ECS Transactions, 2011, 41, 175-187.	0.5	0
143	Size-Dependent Trapping Effect in Nano-Dot Non-Volatile Memory. ECS Transactions, 2011, 41, 121-132.	0.5	0
144	Thermoelectric Characteristics of Annealed N-Type BiTe Thin Film. ECS Transactions, 2012, 41, 27-36.	0.5	0

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145	A low operating voltage IGZO TFT using LaLuO ₃ gate dielectric. , 2013, , .		0
146	GeO ₂ /PZT resistive random access memory devices with Ni electrode. , 2013, , .		0
147	Current uniformity improvement in flexible resistive memory. , 2013, , .		0
148	Flexible InGaZnO TFTs with stacked GeO ₂ /TiO ₂ gate dielectrics. , 2013, , .		0
149	On the variability of threshold voltage window in gate-injection versatile memories with Sub-60mV/dec subthreshold swing and 10 ¹² -cycling endurance. , 2016, , .		0
150	The new FCL with HTS for the high-speed communication system. Microwave and Optical Technology Letters, 2017, 59, 964-966.	1.4	0
151	Improved electrical characteristics and reliability of multi-stacking PNPJ junctionless transistors using channel depletion effect. , 2017, , .		0
152	High speed negative capacitance ferroelectric memory. , 2017, , .		0
153	Photocapacitive effect of ferroelectric hafnium-zirconate capacitor structure. , 2017, , .		0
154	Editorial: IEDMS 2016. Microelectronics Reliability, 2018, 83, 207.	1.7	0
155	Gamma-Ray Irradiation Effect on Ferroelectric Devices with Hafnium Aluminum Oxides. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900414.	2.4	0
156	Ferroelectric Characterization of Hafnium-Oxide-Based Ferroelectric Memories with Remote Nitrogen Plasma Treatments. , 2019, , .		0
157	Simulation of Poly-Silicon Thin Film Transistors with Negative Capacitance Effect. , 2019, , .		0
158	Performance investigation of hafnium-oxide negative capacitance transistor with remote nitrogen plasma treatment. Thin Solid Films, 2022, 755, 139345.	1.8	0